

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A process for the deposition of films on substrates by sputtering or magnetron sputtering, ~~especially~~ for the fabrication of multilayer systems, comprising the step of:

regulating a working gas pressure, a distance between a target and a substrate, or a combination thereof ~~at least at one~~ in a first deposition stage of a new thin film so that the mean free path of particles is chosen smaller than the distance between target and substrate, and regulating the working gas pressure, the distance between target and substrate, or a combination thereof in a subsequent deposition stage of the new thin film so that the mean free path of particles is chosen larger than the distance between target and substrate.

2. (canceled).

3. (currently amended): A process for the deposition of films on substrates by sputtering or magnetron sputtering for the fabrication of multilayer systems, comprising the steps of:

choosing a working gas pressure and a distance between a target and a substrate ~~at least at one deposition stage~~ to result in a product of pressure in Pa and distance in cm being larger than about 2.0 cmPa in a first deposition stage of a new thin film and smaller than about 2.0 cmPa in a subsequent deposition stage of the new thin film, ~~and~~

~~fabricating a multilayer system, including two or more layers and having at least one layer resulting from the at least one deposition stage.~~

4 - 5. (canceled).

6. (original): A process as claimed in claim 1, wherein magnetron sputtering is utilized, and wherein the magnetron is operated in an unbalanced mode in at least one deposition stage.

7. (canceled).

8. (original): A process as claimed in claim 3, wherein magnetron sputtering is utilized, and wherein the magnetron is operated in an unbalanced mode in at least one deposition stage.

9. (canceled).

10. (original): A process as claimed in claim 1, wherein at least one deposition stage is performed with ion beam assistance, or wherein the thin film is polished by ion beam polishing after deposition, or wherein at least one deposition stage is done by electron beam evaporation, or wherein a bias voltage is applied to the substrate during at least one deposition stage, or wherein the distance between target and substrate is about 25 cm or more, or wherein krypton is used as a working gas and wherein the krypton ions have an energy of about 50 eV to 1000 eV, or any combination thereof.

11. (canceled).

12. (original): A process as claimed in claim 3, wherein at least one deposition stage is performed with ion beam assistance, or wherein the thin film is polished by ion beam polishing after deposition, or wherein at least one deposition stage is done by electron beam evaporation, or wherein a bias voltage is applied to the substrate during at least one deposition stage, or wherein the distance between target and substrate is about 25 cm or more, or wherein krypton is used as a working gas and wherein the krypton ions have an energy of about 50 eV to 1000 eV, or any combination thereof.

13. (canceled).

14. (original): A process as claimed in claim 1, wherein at least one deposition stage a plasma is ignited in proximity of the target, a magnetic field is applied in proximity of the ignited plasma and the target oriented in a way that the magnetic field lines extend to the substrate's surface and a voltage of about 200 V or less is applied between plasma source and target.

15. (original): A process as claimed in claim 3, wherein at least one deposition stage a plasma is ignited in proximity of the target, a magnetic field is applied in proximity of the ignited plasma and the target oriented in a way that the magnetic field lines extend to the substrate's surface and a voltage of about 200 V or less is applied between plasma source and target.

16. (original): A process as claimed in claim 14, wherein the plasma source is a magnetron, or wherein the surface to be etched is biased to about -50 V to -2000 V, or a combination thereof.

17. (original): A process as claimed in claim 15, wherein the plasma source is a magnetron, or wherein the surface to be etched is biased to about -50 V to -2000 V, or a combination thereof.

18 - 38. (canceled).